TOSHIBA Transistor Silicon PNP Epitaxial (PCT process)

2SA1298

Low Frequency Power Amplifier Application Power Switching Applications

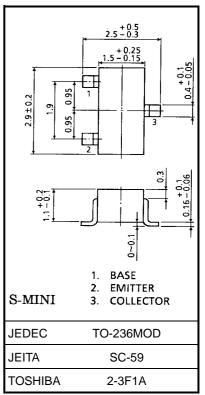
- High DC current gain: hFE = 100~320
- Low saturation voltage: $V_{CE (sat)} = -0.4 V (max)$

 $(I_C = -500 \text{ mA}, I_B = -20 \text{ mA})$

- Suitable for driver stage of small motor
- Complementary to 2SC3265
- Small package

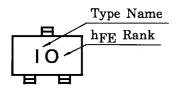
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-30	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-800	mA
Base current	Ι _Β	-160	mA
Collector power dissipation	P _C	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C



Weight: 0.012 g (typ.)

Marking



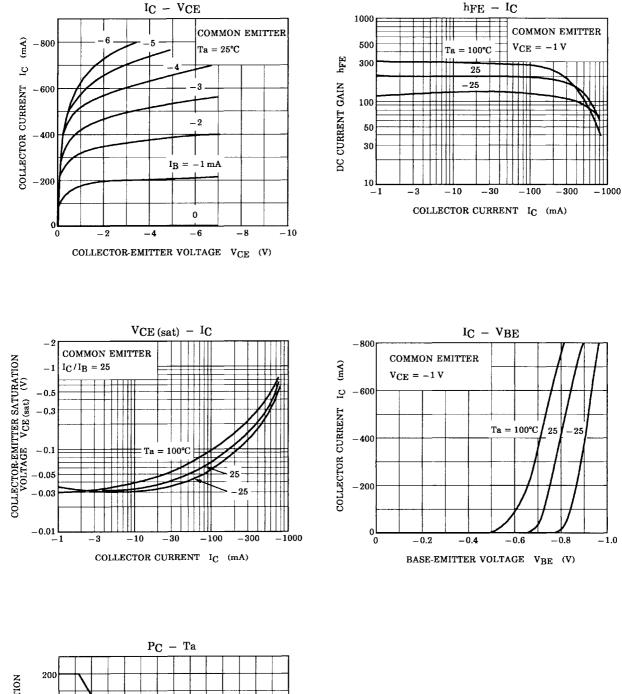
Unit: mm

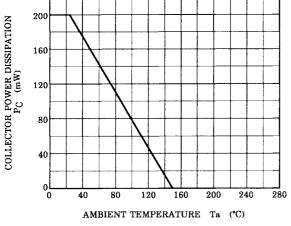
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -30 \text{ V}, \ I_E = 0$	_		-0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = -50 \text{ V}, I_C = 0$	_	_	-0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	$I_{C} = -10 \text{ mA}, I_{B} = 0$	-25	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_{E} = -0.1 \text{ mA}, I_{C} = 0$	-5	_		V
DC current gain	h _{FE (1)} (Note)	$V_{CE} = -1 V, I_C = -100 mA$	100	_	320	
	h _{FE (2)}	$V_{CE} = -1 \text{ V}, I_{C} = -800 \text{ mA}$	40			
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = -500 \text{ mA}, I_{B} = -20 \text{ mA}$	_		-0.4	V
Base-emitter voltage	V _{BE}	$V_{CE} = -1 V, I_{C} = -10 mA$	-0.5		-0.8	V
Transition frequency	fT	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -10 \text{ mA}$		120		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz		13		pF

Note: h_{FE (1)} classification O: 100~200, Y: 160~320

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